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## Features

- Very high speed: 45 ns
- Wide voltage range: 2.2 V to 3.6 V, 4.5 V to 5.5 V
- Ultra low standby power
  - Typical standby current: 3.5  $\mu$ A
  - Maximum standby current: 8.7  $\mu$ A
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- Automatic power-down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 32-pin thin small outline package (TSOP II) and 32-pin small-outline integrated circuit (SOIC) packages

## Functional Description

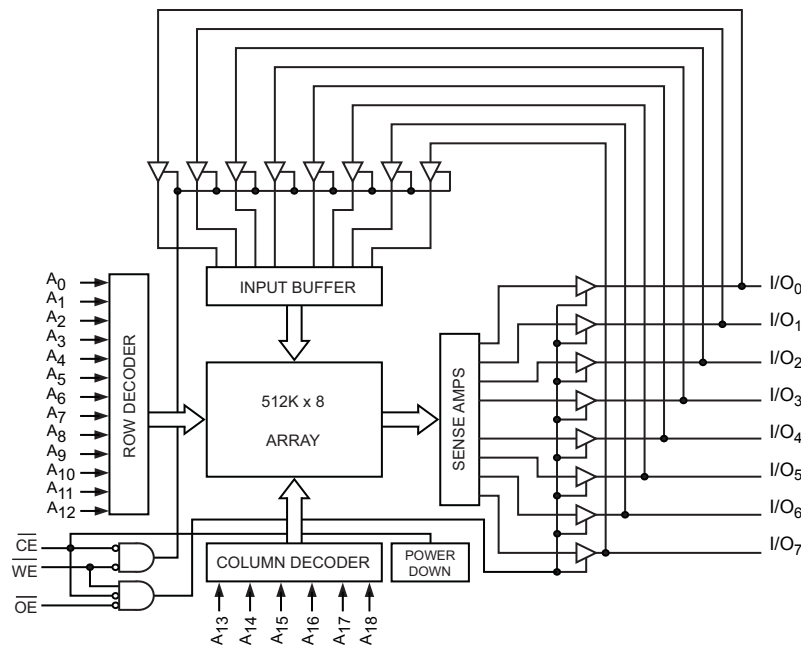
The CY62148GN is a high-performance CMOS static RAM organized as 512K words by 8-bits. This device features advanced circuit design to provide ultra low standby current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications. The device also has an automatic power-down feature that significantly reduces power consumption when addresses are not toggling. Placing the device in standby mode reduces power consumption by more than 99% when deselected ( $\overline{CE}$  HIGH). The eight input and output pins (I/O<sub>0</sub> through I/O<sub>7</sub>) are placed in a high-impedance state when the device is deselected ( $\overline{CE}$  HIGH), Outputs are disabled ( $\overline{OE}$  HIGH), or during an active Write operation ( $\overline{CE}$  LOW and  $\overline{WE}$  LOW).

To write to the device, take Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. Data on the eight I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>) is then written into the location specified on the address pins (A<sub>0</sub> through A<sub>18</sub>).

To read from the device, take Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing Write Enable ( $\overline{WE}$ ) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the I/O pins.

For a complete list of related documentation, [click here](#).

## Logic Block Diagram

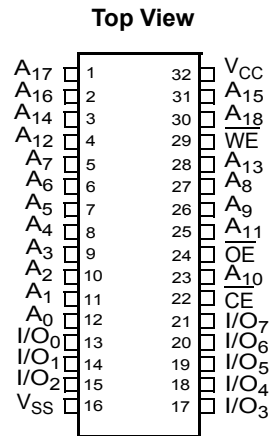


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## Pin Configurations

Figure 1. 32-pin SOIC/TSOP II pinout



## Product Portfolio

Product	Range	V <sub>CC</sub> Range (V)	Speed (ns)	Power Dissipation					
				Operating I <sub>CC</sub> (mA)				Standby I <sub>SB2</sub> (μA)	
				f = 1 MHz		f = f <sub>max</sub>			
				Typ <sup>[1]</sup>	Max	Typ <sup>[1]</sup>	Max	Typ <sup>[1]</sup>	Max
CY62148GN30	Industrial	2.2 V–3.6 V	45	–	6	–	20	3.5	8.7
CY62148GN		4.5 V–5.5 V							

**Note**

1. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.

## Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature	–65 °C to + 150 °C
Ambient temperature with power applied	–55 °C to + 125 °C
Supply voltage to ground potential	–0.5 V to V <sub>CC</sub> + 0.5 V
DC voltage applied to outputs in high Z state <sup>[2, 3]</sup>	–0.5 V to V <sub>CC</sub> + 0.5 V
DC input voltage <sup>[2, 3]</sup>	–0.5 V to V <sub>CC</sub> + 0.5 V

Output current into outputs (LOW)	20 mA
Static discharge voltage (per MIL-STD-883, Method 3015)	> 2001 V
Latch-up current	> 140 mA

## Operating Range

Device	Range	Ambient Temperature	V <sub>CC</sub> <sup>[4]</sup>
CY62148GN	Industrial	–40 °C to +85 °C	2.2 V to 3.6 V, 4.5 V to 5.5 V

## Electrical Characteristics

Over the operating range

Parameter	Description	Test Conditions	45 ns			Unit
			Min	Typ <sup>[5]</sup>	Max	
V <sub>OH</sub>	Output HIGH voltage	2.2 V to 2.7 V V <sub>CC</sub> = Min, I <sub>OH</sub> = –0.1 mA	2	–	–	V
		2.7 V to 3.6 V V <sub>CC</sub> = Min, I <sub>OH</sub> = –1.0 mA	2.4	–	–	
		4.5 V to 5.5 V V <sub>CC</sub> = Min, I <sub>OH</sub> = –1.0 mA	2.4	–	–	
		4.5 V to 5.5 V V <sub>CC</sub> = Min, I <sub>OH</sub> = –0.1 mA	V <sub>CC</sub> – 0.5 <sup>[6]</sup>	–	–	
V <sub>OL</sub>	Output LOW voltage	2.2 V to 2.7 V V <sub>CC</sub> = Min, I <sub>OL</sub> = 0.1 mA	–	–	0.4	V
		2.7 V to 3.6 V V <sub>CC</sub> = Min, I <sub>OL</sub> = 2.1 mA	–	–	0.4	
		4.5 V to 5.5 V V <sub>CC</sub> = Min, I <sub>OL</sub> = 2.1 mA	–	–	0.4	
V <sub>IH</sub>	Input HIGH voltage	2.2 V to 2.7 V	1.8	–	V <sub>CC</sub> + 0.3 <sup>[3]</sup>	V
		2.7 V to 3.6 V	2	–	V <sub>CC</sub> + 0.3 <sup>[3]</sup>	
		4.5 V to 5.5 V	2.2	–	V <sub>CC</sub> + 0.5	
V <sub>IL</sub>	Input LOW voltage	2.2 V to 2.7 V	–0.3 <sup>[2]</sup>	–	0.6	V
		2.7 V to 3.6 V	–0.3 <sup>[2]</sup>	–	0.8	
		4.5 V to 5.5 V	–0.5	–	0.8	
I <sub>IX</sub>	Input leakage current	GND ≤ V <sub>I</sub> ≤ V <sub>CC</sub>	–1	–	+1	μA
I <sub>OZ</sub>	Output leakage current	GND ≤ V <sub>O</sub> ≤ V <sub>CC</sub> , output disabled	–1	–	+1	μA
I <sub>CC</sub>	V <sub>CC</sub> operating supply current	f = f <sub>max</sub> = 1/t <sub>RC</sub> V <sub>CC</sub> = V <sub>CC(max)</sub> , I <sub>OUT</sub> = 0 mA CMOS levels	–	–	20	mA
		f = 1 MHz	–	–	6	
I <sub>SB1</sub> <sup>[7]</sup>	Automatic $\overline{CE}$ power-down current – CMOS inputs	$\overline{CE} \geq V_{CC} - 0.2 V$ , $V_{IN} \geq V_{CC} - 0.2 V$ or $V_{IN} \leq 0.2 V$ , f = f <sub>max</sub> (address and data only), f = 0 ( $\overline{OE}$ and $\overline{WE}$ ) V <sub>CC</sub> = V <sub>CC(max)</sub>	–	3.5	8.7	μA
I <sub>SB2</sub> <sup>[7]</sup>	Automatic $\overline{CE}$ power-down current – CMOS inputs	$\overline{CE} \geq V_{CC} - 0.2 V$ , $V_{IN} \geq V_{CC} - 0.2 V$ or $V_{IN} \leq 0.2 V$ , f = 0, V <sub>CC</sub> = V <sub>CC(max)</sub>	–	3.5	8.7	μA

### Notes

- V<sub>IL(min)</sub> = –2.0 V for pulse durations less than 20 ns.
- V<sub>IH(max)</sub> = V<sub>CC</sub> + 0.75 V for pulse durations less than 20 ns.
- Full device AC operation assumes a minimum of 100 μs ramp time from 0 to V<sub>CC(min)</sub> and 200 μs wait time after V<sub>CC</sub> stabilization.
- Typical values are included for reference and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.
- This parameter is guaranteed by design and not tested.
- Chip enable ( $\overline{CE}$ ) must be HIGH at CMOS level to meet the I<sub>SB2</sub> / I<sub>CCDR</sub> spec. Other inputs can be left floating.

## Capacitance

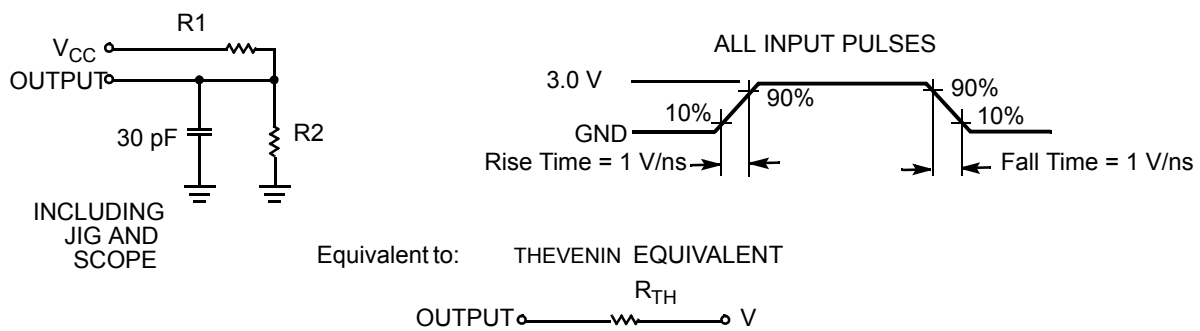
Parameter [8]	Description	Test Conditions	Max	Unit
$C_{IN}$	Input capacitance	$T_A = 25\text{ }^\circ\text{C}$ , $f = 1\text{ MHz}$ , $V_{CC} = V_{CC(Typ)}$	10	pF
$C_{OUT}$	Output capacitance		10	pF

## Thermal Resistance

Parameter [8]	Description	Test Conditions	32-pin SOIC Package	32-pin TSOP II Package	Unit
$\Theta_{JA}$	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	51.79	79.03	$^\circ\text{C/W}$
$\Theta_{JC}$	Thermal resistance (junction to case)		25.12	17.44	$^\circ\text{C/W}$

## AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms<sup>[9]</sup>



Parameter <sup>[8]</sup>	2.5 V	3.0 V	5.0 V	Unit
R1	16667	1103	1800	$\Omega$
R2	15385	1554	990	$\Omega$
$R_{TH}$	8000	645	639	$\Omega$
$V_{TH}$	1.20	1.75	1.77	V

### Notes

- Tested initially and after any design or process changes that may affect these parameters.
- Full-device operation requires linear  $V_{CC}$  ramp from VDR to  $V_{CC(min)} > 100\ \mu\text{s}$  or stable at  $V_{CC(min)} > 100\ \mu\text{s}$ .

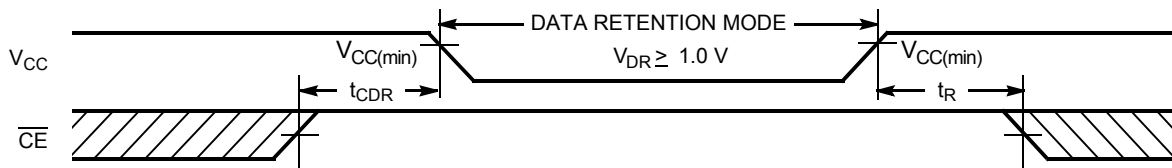
## Data Retention Characteristics

Over the operating range

Parameter	Description	Conditions	Min	Typ <sup>[10]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention		1	–	–	V
$I_{CCDR}$ <sup>[11, 12]</sup>	Data retention current	$V_{CC} = 1.2V, \overline{CE} \geq V_{CC} - 0.2V,$ $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	–	–	13	$\mu A$
$t_{CDR}$ <sup>[13]</sup>	Chip deselect to data retention time		0	–	–	ns
$t_R$ <sup>[13, 14]</sup>	Operation recovery time		45	–	–	ns

## Data Retention Waveform

Figure 3. Data Retention Waveform



### Notes

10. Typical values are included for reference and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25^\circ C$ .
11. Chip enable ( $\overline{CE}$ ) must be HIGH at CMOS level to meet the  $I_{SB2} / I_{CCDR}$  spec. Other inputs can be left floating.
12.  $I_{CCDR}$  is guaranteed only after device is first powered up to  $V_{CC(min)}$  and then brought down to  $V_{DR}$ .
13. These parameters are guaranteed by design.
14. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)} > 100 \mu s$  or stable at  $V_{CC(min)} > 100 \mu s$ .

## Switching Characteristics

Over the operating range

Parameter <sup>[15]</sup>	Description	45 ns		Unit
		Min	Max	
<b>Read Cycle</b>				
$t_{RC}$	Read cycle time	45	–	ns
$t_{AA}$	Address to data valid	–	45	ns
$t_{OHA}$	Data hold from address change	10	–	ns
$t_{ACE}$	$\overline{CE}$ LOW to data valid	–	45	ns
$t_{DOE}$	$\overline{OE}$ LOW to data valid	–	22	ns
$t_{LZOE}$	$\overline{OE}$ LOW to low Z <sup>[16]</sup>	5	–	ns
$t_{HZOE}$	$\overline{OE}$ HIGH to high Z <sup>[16, 17]</sup>	–	18	ns
$t_{LZCE}$	$\overline{CE}$ LOW to low Z <sup>[16]</sup>	10	–	ns
$t_{HZCE}$	$\overline{CE}$ HIGH to high Z <sup>[16, 17]</sup>	–	18	ns
$t_{PU}$	$\overline{CE}$ LOW to power-up	0	–	ns
$t_{PD}$	$\overline{CE}$ HIGH to power-down	–	45	ns
<b>Write Cycle<sup>[18, 19]</sup></b>				
$t_{WC}$	Write cycle time	45	–	ns
$t_{SCE}$	$\overline{CE}$ LOW to write end	35	–	ns
$t_{AW}$	Address setup to write end	35	–	ns
$t_{HA}$	Address hold from write end	0	–	ns
$t_{SA}$	Address setup to write start	0	–	ns
$t_{PWE}$	$\overline{WE}$ pulse width	35	–	ns
$t_{SD}$	Data setup to write end	25	–	ns
$t_{HD}$	Data hold from write end	0	–	ns
$t_{HZWE}$	$\overline{WE}$ LOW to high Z <sup>[16, 17]</sup>	–	18	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to low Z <sup>[16]</sup>	10	–	ns

### Notes

15. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3 V, and output loading of the specified  $I_{OL}/I_{OH}$  as shown in the [Figure 2 on page 5](#).
16. At any temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any device.
17.  $t_{HZOE}$ ,  $t_{HZCE}$ , and  $t_{HZWE}$  transitions are measured when the outputs enter a high impedance state.
18. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE} = V_{IL}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing should be referenced to the edge of the signal that terminates the write.
19. The minimum write cycle pulse width for Write Cycle No. 3 ( $\overline{WE}$  controlled,  $\overline{OE}$  LOW) should be equal to the sum of  $t_{SD}$  and  $t_{HZWE}$ .



### Switching Waveforms

Figure 4. Read Cycle No. 1 (Address Transition Controlled) [20, 21]

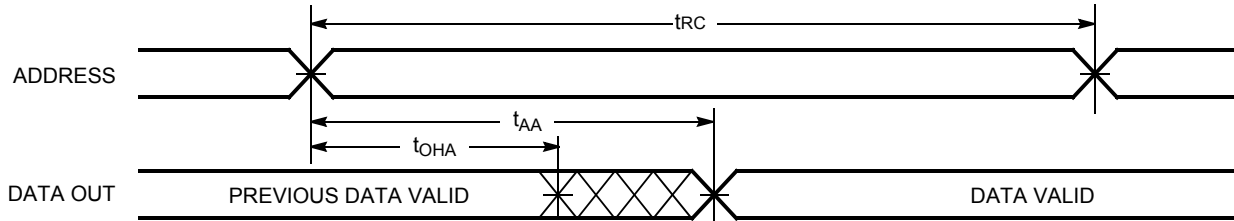


Figure 5. Read Cycle No. 2 ( $\overline{OE}$  Controlled) [21, 22]

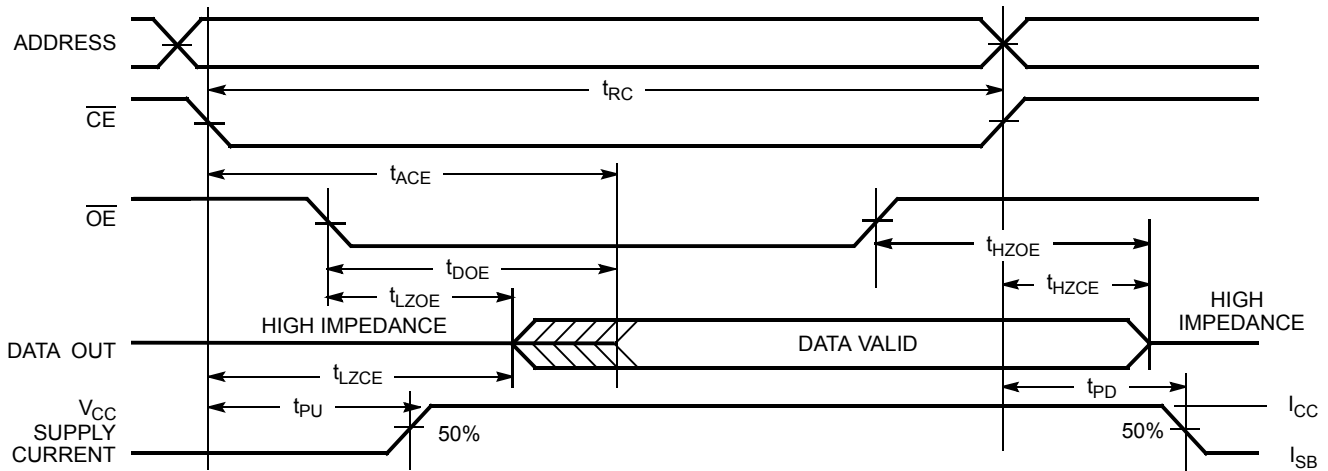
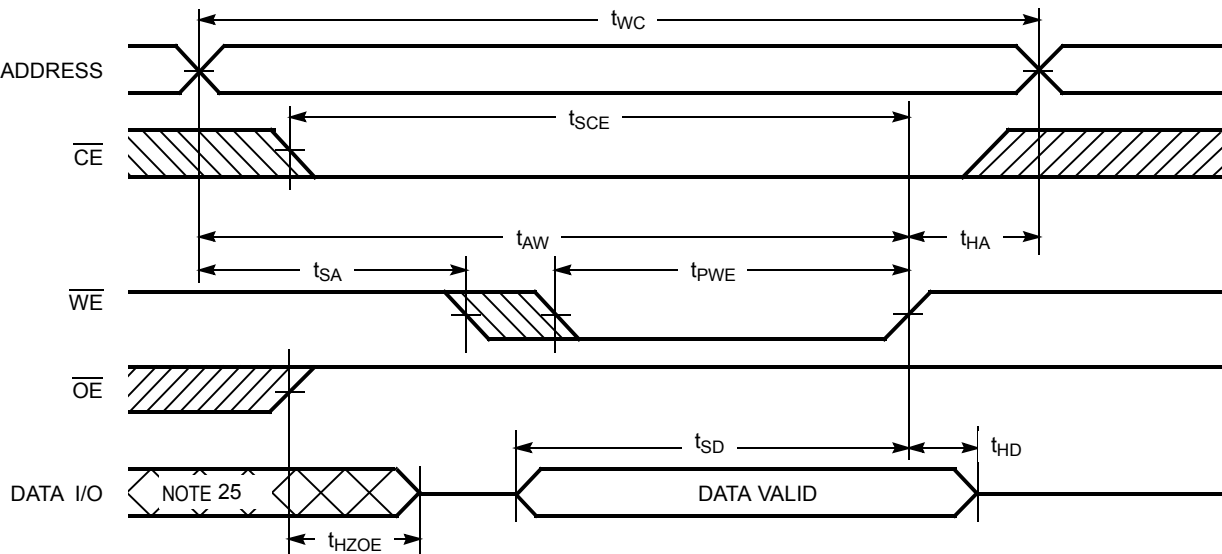


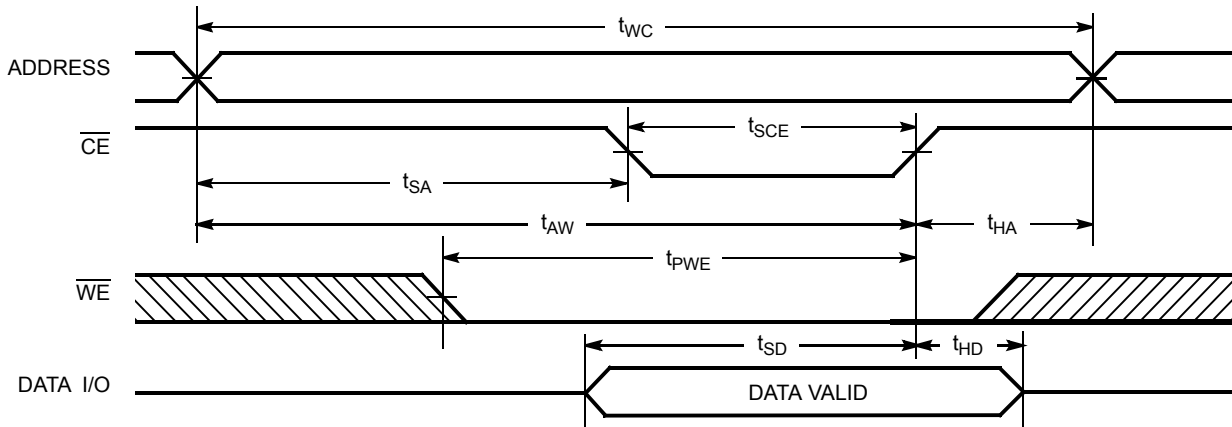
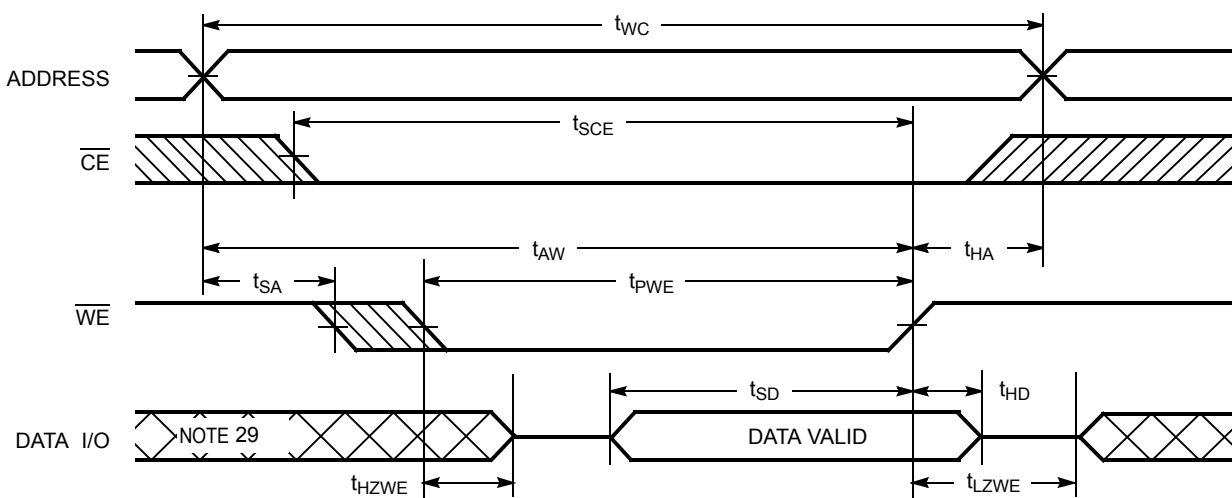
Figure 6. Write Cycle No. 1 ( $\overline{WE}$  Controlled,  $\overline{OE}$  HIGH During Write) [23, 24]



**Notes**

- 20. Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE}$  =  $V_{IL}$ .
- 21.  $\overline{WE}$  is HIGH for read cycles.
- 22. Address valid before or similar to  $\overline{CE}$  transition LOW.
- 23. Data I/O is high impedance if  $\overline{OE}$  =  $V_{IH}$ .
- 24. If  $\overline{CE}$  goes HIGH simultaneously with  $\overline{WE}$  HIGH, the output remains in high impedance state.
- 25. During this period, the I/Os are in output state and input signals must not be applied.

**Switching Waveforms** (continued)

**Figure 7. Write Cycle No. 2 ( $\overline{\text{CE}}$  Controlled)** [26, 27]

**Figure 8. Write Cycle No. 3 ( $\overline{\text{WE}}$  Controlled,  $\overline{\text{OE}}$  LOW)** [27, 28]

**Notes**

26. Data I/O is high impedance if  $\overline{\text{OE}} = V_{\text{IH}}$ .

27. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  HIGH, the output remains in high impedance state.

28. The minimum write cycle pulse width should be equal to the sum of  $t_{\text{SD}}$  and  $t_{\text{HZWE}}$ .

29. During this period, the I/Os are in output state and input signals must not be applied.

**Truth Table**

$\overline{\text{CE}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	I/O	Mode	Power
H <sup>[30]</sup>	X	X	High Z	Deselect/power-down	Standby ( $I_{\text{SB}}$ )
L	H	L	Data out	Read	Active ( $I_{\text{CC}}$ )
L	L	X	Data in	Write	Active ( $I_{\text{CC}}$ )
L	H	H	High Z	Selected, outputs disabled	Active ( $I_{\text{CC}}$ )

**Note**

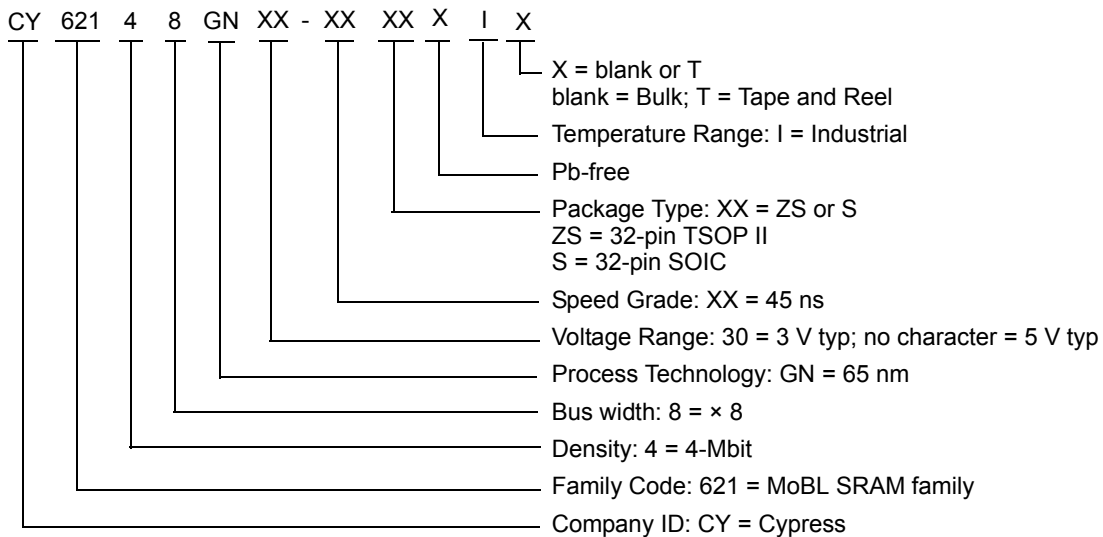
30. Chip enable ( $\overline{\text{CE}}$ ) must be HIGH at CMOS level to meet the  $I_{\text{SB2}} / I_{\text{CCDR}}$  spec. Other inputs can be left floating.

## Ordering Information

Table 1. Key features and Ordering Information

Speed (ns)	Voltage Range (V)	Ordering Code	Package Diagram	Package Type	Operating Range
45	2.2 V–3.6 V	CY62148GN30-45ZSXI	51-85095	32-pin TSOP II (Pb-free)	Industrial
		CY62148GN30-45ZSXIT	51-85095	32-pin TSOP II (Pb-free), Tape and Reel	
		CY62148GN30-45SXI	51-85081	32-pin SOIC (Pb-free)	
		CY62148GN30-45SXIT	51-85081	32-pin SOIC (Pb-free), Tape and Reel	
	4.5 V–5.5 V	CY62148GN-45ZSXI	51-85095	32-pin TSOP II (Pb-free)	
		CY62148GN-45ZSXIT	51-85095	32-pin TSOP II (Pb-free), Tape and Reel	
		CY62148GN-45SXI	51-85081	32-pin SOIC (Pb-free)	
		CY62148GN-45SXIT	51-85081	32-pin SOIC (Pb-free), Tape and Reel	

## Ordering Code Definitions



Package Diagrams

Figure 9. 32-pin TSOP II (20.95 × 11.76 × 1.0 mm) ZS32 Package Outline, 51-85095

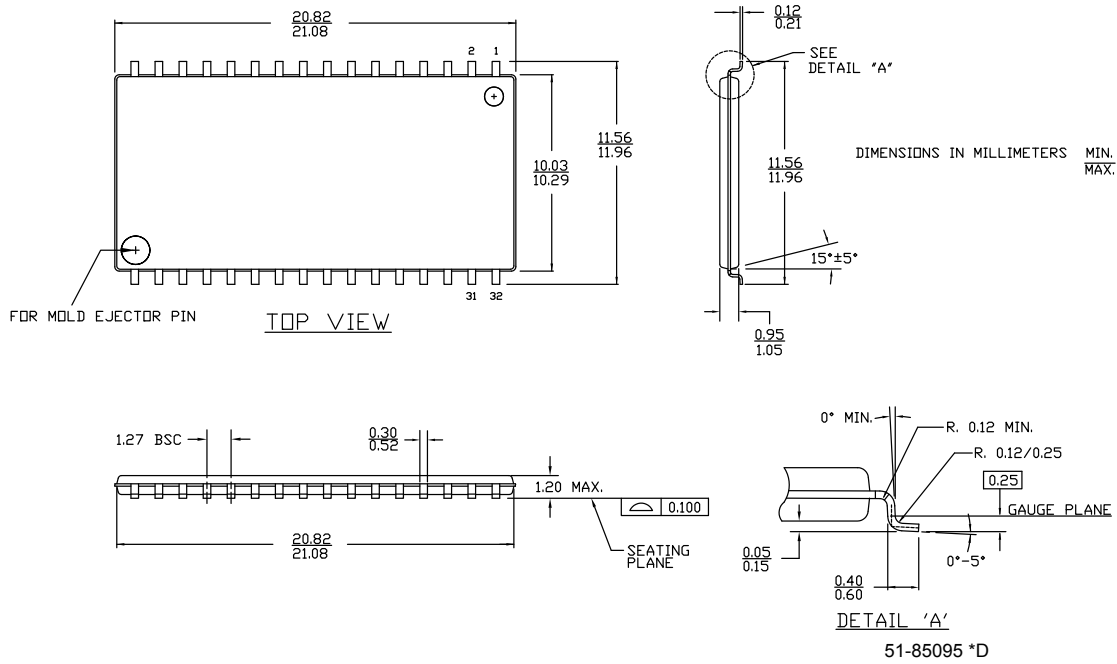
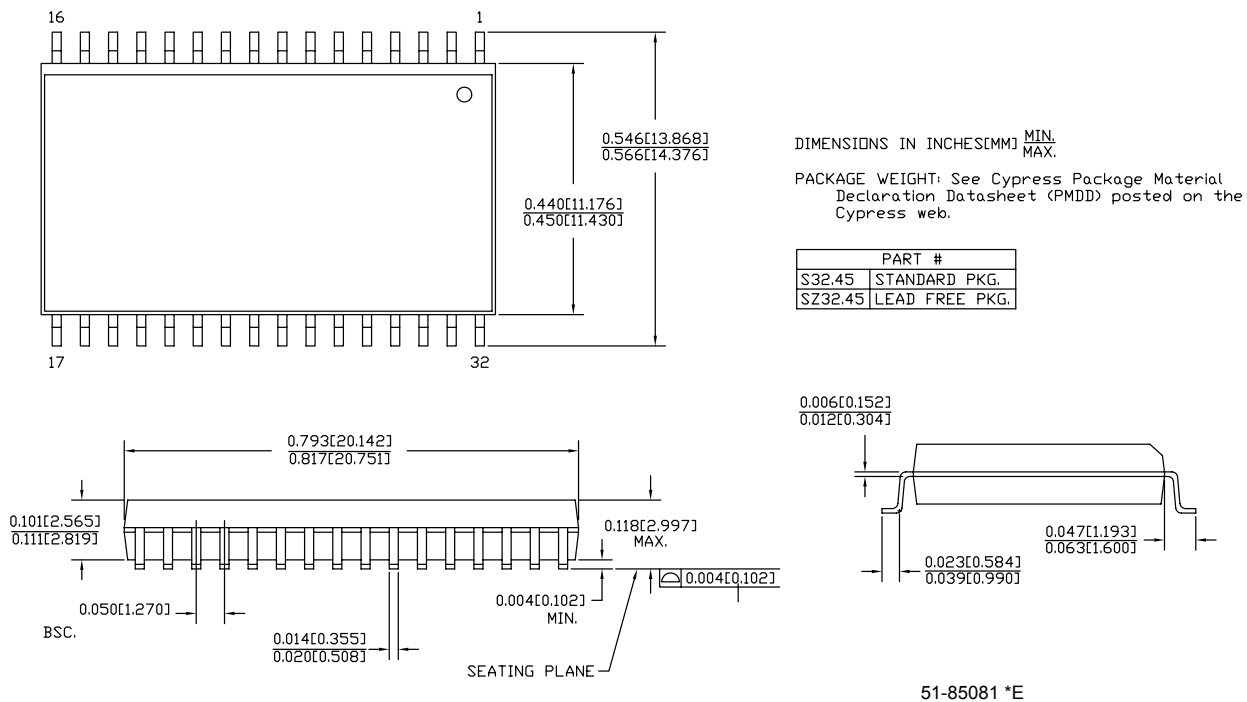


Figure 10. 32-pin SOIC (450 Mils) S32.45/SZ32.45 Package Outline, 51-85081



## Acronyms

**Table 2. Acronyms Used in this Document**

Acronym	Description
CE	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
OE	output enable
MoBL	More Battery Life
SOIC	small outline integrated circuit
SRAM	static random access memory
TSOP	thin small outline package
WE	write enable

## Document Conventions

### Units of Measure

**Table 3. Units of Measure**

Symbol	Unit of Measure
°C	Degrees Celsius
MHz	megahertz
μA	microamperes
μs	microseconds
mA	milliamperes
ns	nanoseconds
Ω	ohms
%	percent
pF	picofarads
V	volts
W	watts

## Document History Page

Document Title: CY62148GN MoBL <sup>®</sup> , 4-Mbit (512K × 8) Static RAM				
Document Number: 001-95418				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	5056496	NILE	12/29/2015	New data sheet.
*A	5092456	NILE	01/19/2016	Added "2.2 V to 3.6 V" range related information in all instances across the document. Updated <a href="#">Ordering Information</a> : Updated part numbers.
*B	5422041	NILE	09/09/2016	Updated <a href="#">Electrical Characteristics</a> : Changed minimum value of V <sub>OH</sub> parameter corresponding to "2.7 V to 3.6 V" from 2.2 V to 2.4 V. Changed minimum value of V <sub>IH</sub> parameter corresponding to "2.2 V to 2.7 V" from 2.0 V to 1.8 V. Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated Disclaimer. Updated to new template.
*C	5546908	NILE	12/08/2016	Updated <a href="#">Ordering Information</a> : No change in part numbers. Removed Disclaimer (text referencing to contact sales). Completing Sunset Review.
*D	6002325	AESATMP9	12/21/2017	Updated logo and copyright.